





COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage V_{GS(th)} <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- ESD Protected Gate to 2.5kV HBM
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

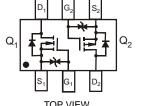
- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 7
- Ordering Information: See Page 7
- Weight: 0.006 grams (approximate)

SOT-563









TOP VIEW

BOTTOM VIEW Internal Schematic

Maximum Ratings N-CHANNEL – Q_1 @ $T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±6	V
Drain Current (Note 1) $ T_A = 25^{\circ}\text{C} $ $ T_A = 85^{\circ}\text{C} $	ln ln	870 630	mA

Maximum Ratings P-CHANNEL − Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±6	V
Drain Current (Note 1) $T_A = T_A =$	ln.	-640 -460	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_{D}	530	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	235	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.



Electrical Characteristics N-CHANNEL – Q₁ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	± 1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)			_	_	_		
Gate Threshold Voltage	V _{GS(th)}	0.5	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
			0.3	0.4		$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	0.4	0.5	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
			0.5	0.7		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y _{fs}		1.4	_	S	$V_{DS} = 10V, I_D = 400 \text{mA}$	
Diode Forward Voltage (Note 4)			0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	_	60.67	_	pF		
Output Capacitance	Coss	_	9.68	_	pF	$V_{DS} = 16V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	5.37	_	pF	1 = 1.0ivii iz	
Total Gate Charge	Qg	_	736.6	_		1/ 45\/\/ 40\/	
Gate-Source Charge	Q _{qs}	_	93.6	_	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q _{gd}	_	116.6	_		$I_D = 250 \text{mA}$	
Turn-On Delay Time	t _{d(on)}		5.1	_		101/1/	
Turn-On Rise Time	t _r	_	7.4	_		$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{d(off)}	_	26.7	_	ns	$R_L = 47\Omega$, $R_G = 10\Omega$, $I_D = 200$ mA	
Turn-Off Fall Time	t _f		12.3	_		ID = ZUUIIA	

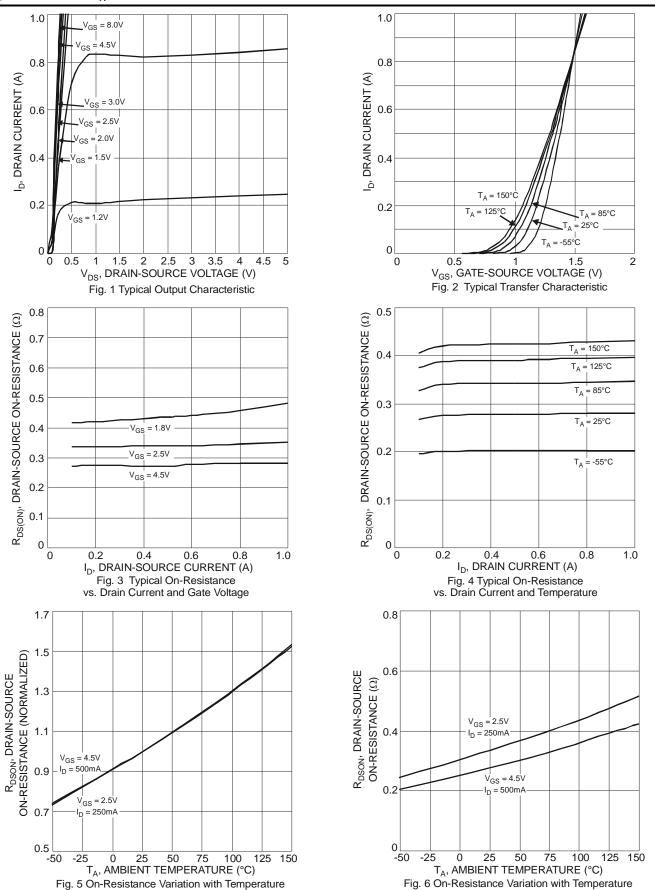
Electrical Characteristics P-CHANNEL - Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-100	nA	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	± 2.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)	<u> </u>						
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	0.5 0.7 1.0	0.7 0.9 1.3	Ω	$V_{GS} = -4.5V$, $I_D = -430$ mA $V_{GS} = -2.5V$, $I_D = -300$ mA $V_{GS} = -1.8V$, $I_D = -150$ mA	
Forward Transfer Admittance	Y _{fs}	_	-0.9	_	S	$V_{DS} = 10V, I_{D} = -250 \text{mA}$	
Diode Forward Voltage (Note 4)		_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$	
DYNAMIC CHARACTERISTICS			_	_	_		
Input Capacitance	C _{iss}		59.76	_	pF	101/11/	
Output Capacitance	Coss		12.07	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	6.36	_	pF	1 = 1.0WII IZ	
Total Gate Charge	Q_g		622.4	_		\\ 4.5\\\\ 10\\	
Gate-Source Charge	Q_{gs}		100.3	_	рC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -250\text{mA}$	
Gate-Drain Charge	Q_{gd}		132.2	_		ID = -230IIIA	
Turn-On Delay Time	t _{d(on)}		5.1	_		\\ 40\\\\\	
Turn-On Rise Time	t _r		8.1	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$ $R_L = 47\Omega, R_G = 10\Omega,$	
Turn-Off Delay Time	t _{d(off)}		28.4	_	115	$R_L = 4752, R_G = 1052,$ $I_D = -200 \text{mA}$	
Turn-Off Fall Time	t _f	_	20.7	_		10 = -200111A	

Notes: 4. Short duration pulse test used to minimize self-heating effect.



N-CHANNEL - Q₁





N-CHANNEL - Q₁ (continued)

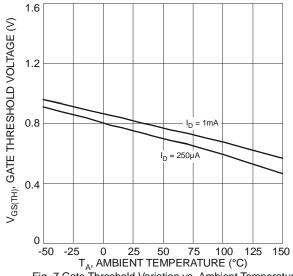
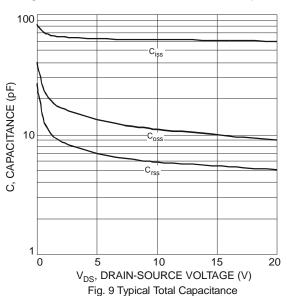


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



1.0 0.8 IS, SOURCE CURRENT (A) T_A = 25°C 0.6 0.2 0 $\begin{array}{ccc} 0.4 & 0.6 & 0.8 & 1.0 \\ V_{SD}, \text{SOURCE-DRAIN VOLTAGE (V)} \end{array}$ 0.2 1.2 Fig. 8 Diode Forward Voltage vs. Current

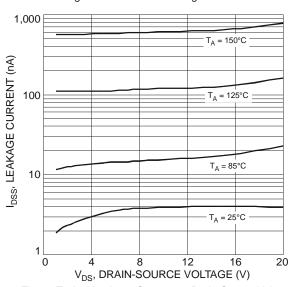


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

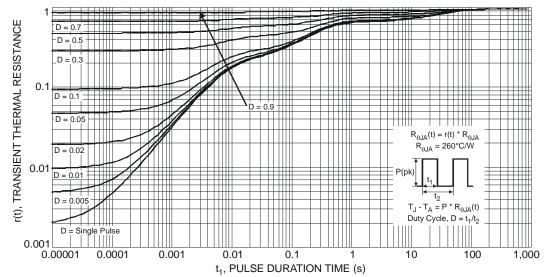
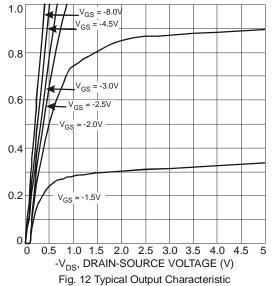


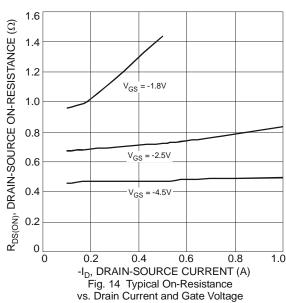
Fig. 11 Transient Thermal Response

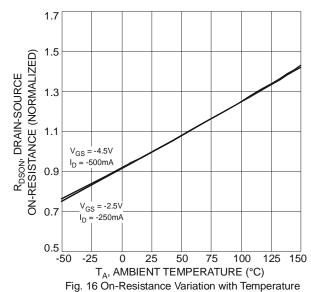
3.0



P-CHANNEL - Q₂







(E) LNBUNCORRE O.6

O.2

T_A = 150°C

T_A = 25°C

T_A = 25°C

T_A = 25°C

T_A = 55°C

O.5

-V_{GS}, GATE-SOURCE VOLTAGE (V)

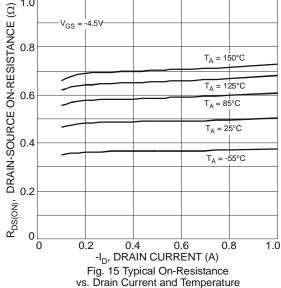
Fig. 13 Typical Transfer Characteristic

(C) T_A = 150°C

1.0

0.8

 $V_{DS} = -5V$



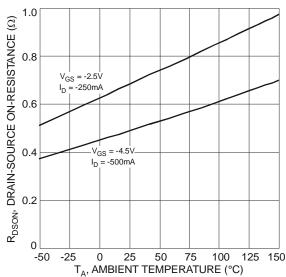
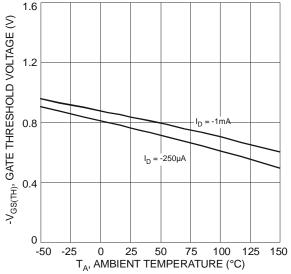
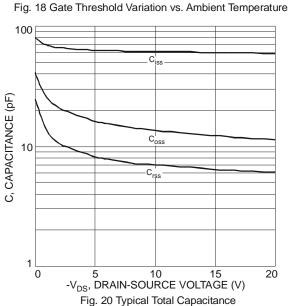


Fig. 17 On-Resistance Variation with Temperature

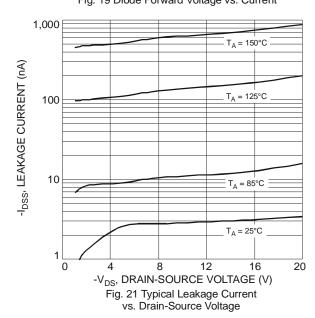


P-CHANNEL - Q₂ (continued)





1.0 0.8 -I_S, SOURCE CURRENT (A) .T_A = 25°C 0.6 0.4 0.2 0 0.2 0.4 0.6 8.0 1.0 $-V_{SD}$, SOURCE-DRAIN VOLTAGE (V) Fig. 19 Diode Forward Voltage vs. Current



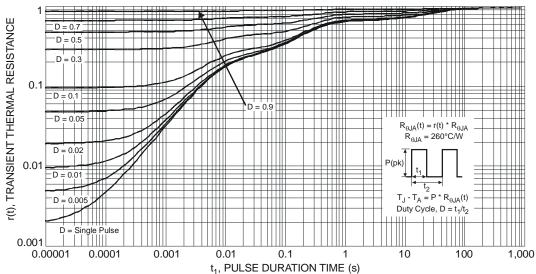


Fig. 22 Transient Thermal Response

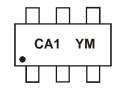


Ordering Information (Note 5)

Part Number	Case	Packaging
DMG1016V-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



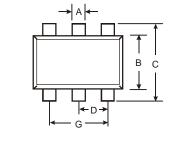
CA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

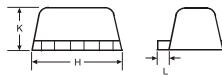
Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

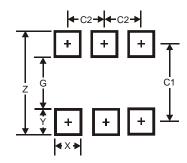
Package Outline Dimensions





SOT-563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
М	0.10	0.18	0.11				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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